HALOGEN FREE



Vishay Siliconix

# 2 Port, USB 2.0 High Speed (480 Mbps) Switch, DPDT Analog Switch

#### **DESCRIPTION**

The DG2720 is 2 Port high speed analog switch optimized for USB 2.0 signal switching. The DG2720 switch is configured in DPDT. It handles bidirectional signal flow, achieving a 620 MHz -3 dB bandwidth with 5 pF load, and a port to port Crosstalk and isolation at -49 dB.

Processed with high density sub micron CMOS, the DG2720 provide low parasitic capacitance. Signals are routed with minimized phase distortion and attain a bit to bit skew is as low as 40 pS.

The DG2720 is designed for a wide range of operating voltages, from 2.7 V to 4.3 V that can be driven directly from one cell Li-ion battery. On-chip circuitry protects against conditions when either the D+/D- lines are shorted to the  $V_{BUS}$  at the USB port. Additionally, logic control pins (S and  $\overline{\text{OE}}$ ) can tolerate the presence of voltages that are above the supply power rail (V+). The control logic threshold is guaranteed to be ( $V_{IH} = 1.3 \text{ V/min}$ ).

Latch up current is greater than 300 mA, as per JESD78, and its ESD tolerance exceeds 8 kV.

Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL rating

As a further sign of Vishay Siliconix's commitment, the DG2720 is fully RoHS complaint.

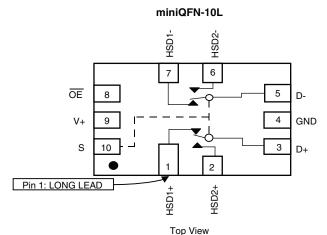
### **FEATURES**

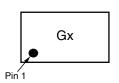
- Wide operation voltage range
- Low on-resistance, 5.7 Ω (typical at 3 V)
- Low capacitance, 5.6 pF (typical)
- 3 dB high bandwidth with 5 pF load:
   620 MHz (typical)
- Low bit to bit skew: 40 pS (typical)
- Low power consumption
- · Low logic threshold: V
- Power down protection: D+/D- pins can tolerate up to 5 V when V+ = 0 V
- Logic (S and OE) above V+ tolerance
- Latch-up current greater than 300 mA per JESD78
- 8 kV ESD protection (HBM)
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **APPLICATIONS**

- · Cellular phones
- · Portable media players
- PDA
- · Digital camera
- GPS
- Notebook computer
- TV, monitor, and set top box

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





Device marking: Gx for DG2720 x = Date/Lot traceability code

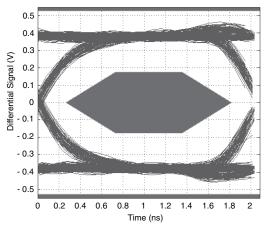
Document Number: 74593



ORDERING INFORMATION					
TEMP RANGE PACKAGE		PART NUMBER			
-40 °C to +85 °C	miniQFN-10	DG2720DN-T1-E4			

TRUTH TABLE					
OE (PIN 8)	DE (PIN 8) S (PIN 10) FUNCTION				
0	0	D+ = HSD1+ and D- = HSD1-			
0	1	D+ = HSD2+ and D- = HSD2-			
1	Х	Disconnect			

PIN DESCRIPTIONS				
PIN NAME	DESCRIPTION			
ŌĒ	Bus Switch Enable			
S	Select Input			
HSD1±, HSD2±, D±	Data Port			



High Speed Signal Quality Eye Diagram Test with V+ = 3.3 V

SUMMARY OF THE USB 2.0 SIGNAL QUALITY TEST RESULTS					
Compliance Test High Speed					
Signal Eye Test	Pass				
EOP Width	7.95 bits				
Measured Signal Rate	480.0009 MHz				
Consecutive Jitter Range	-59.8 ps to 68.2 ps, RMS Jitter 26.8 ps				
Paired JK Jitter Range	-49.7 ps to 51.4 ps, RMS Jitter 25.3 ps				
Paired KJ Jitter Range	-61.3 ps to 58.5 ps, RMS Jitter 26.8 ps				

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER		LIMIT	UNIT		
Reference to GND	V+	-0.3 to +5			
neierence to GND	S, OE, D±, HSD1±, HSD2± a	-0.3 to (V+ + 0.3)	- V		
Current (Any Terminal except S, OE, D±, HSD1±, HSD2±)		30			
Continuous Current (S, OE, D±, HSD1±, HSD2±)		± 250	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 500			
Storage Temperature (D Suffix)		-65 to +150	°C		
Power Dissipation (Packages) <sup>b</sup>	miniQFN-10 <sup>c</sup>	208	mW		
ESD (Human Body Model) I/O to GND		8	kV		
Latch-up (Current Injection)		350	mA		

## Notes

- a. Signals on S, OE, D±, HSD1±, HSD2± exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.6 mW/°C above 70 °C.



# Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS	TEMP. a	<b>LIMITS</b> -40 to +85 °C			UNI
	OTHIBOL	OTHERWISE UNLESS SPECIFIED		MIN. b		MAX. b	ONIT
Analog Switch				L	l		ı
Analog Signal Range <sup>d</sup>	V <sub>ANALOG</sub>	R <sub>DS(on)</sub>	Full	0	-	V+	V
On-Resistance	D	$V+ = 3 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0.4 \text{ V}$	Room	-	5.7	7	
On-nesistance	R <sub>DS(on)</sub>	$V + = 3 V$ , $I_{D\pm} = 0 IIIA$ , $V_{HSD1/2\pm} = 0.4 V$	Full	-	-	9	Ω
On-Resistance Match d	$\Delta R_{ON}$	$V+=3 V$ , $I_{D\pm}=8 mA$ , $V_{HSD1/2\pm}=0.4 V$	Room	-	0.35	-	
On-Resistance Resistance Flatness d	R <sub>ON</sub> Flatness	$V+ = 3 \text{ V}, I_{D\pm} = 8 \text{ mA}, V_{HSD1/2\pm} = 0 \text{ V}, 1 \text{ V}$	Room	-	2	-	
Switch Off Leakage Current	I <sub>(off)</sub>	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 3 \text{ V}, $ $V_{\text{D}\pm} = 3 \text{ V}, 0.3 \text{ V}$	Full	-100	-	100	nA
Channel On Leakage Current	I <sub>(on)</sub>	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 4 \text{ V}, \\ V_{\text{D}\pm} = 4 \text{ V}, 0.3 \text{ V}$	Full	-200	-	200	ПА
Digital Control							
Input Voltage High	$V_{\rm INH}$	V+ = 3 V to 3.6 V	Full	1.3	-	ı	
input voitage riigii	VINH	V+ = 4.3 V	Full	1.7	-	ı	V
Input Voltage Low	$V_{INL}$	V+ = 3 V to 4.3 V	Full	-	-	0.5	
Input Capacitance	C <sub>IN</sub>		Full	-	5.6	-	рF
Input Current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$ or $V+$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Break-Before-Make Time e, d	t <sub>BBM</sub>		Room	-	5	-	ns
Break Before Wake Time	чввм		Full	-	5	-	
Enable Turn-On Time e, d	t <sub>ON(EN)</sub>	V+ = 3 V, $V_{D1/2 \pm}$ = 1.5 V, $R_L$ = 50 Ω,	Room	-	-	30	
Enable fam on fine	*ON(EN)	C <sub>L</sub> = 35 pF	Full	-	-	30	
Enable Turn-Off Time e, d	t		Room	-	-	25	
Chable fulli-Oil fillie	t <sub>OFF(EN)</sub>		Full	-	-	25	
Charge Injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 0 V$		-	0.5	-	рС
Off-Isolation <sup>d</sup>	OIRR	$V+ = 3 V \text{ to } 3.6 V, R_L = 50 \Omega, C_L = 5 pF,$		-	-30	-	dB
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	f = 240 MHz		-	-49	-	ub
Bandwidth <sup>d</sup>	BW	V+ = 3 V to 3.6 V, $R_L$ = 50 Ω, $C_L$ = 5 pF, -3 dB	Room	-	620	-	MHz
Channel-Off Capacitance d	$C_{D1\pm  (off)}$ $C_{D2\pm  (off)}$			-	4	ı	pF
Charmer-On Capacitance		V+ = 3.3 V, f = 1 MHz		-	4	1	
Channel On Canacitanae d	C <sub>D± (off)</sub>	V+ = 3.3 V, I = 1 IVIHZ		-	5.6	-	
Channel-On Capacitance d	C <sub>D± (on)</sub>			-	11	-	
Channel-to-Channel Skew d	t <sub>SK(O)</sub>			-	50	-	ps
Skew Off Opposite Transitions of the Same Output <sup>d</sup>	t <sub>SK(p)</sub>	$V+ = 3 V \text{ to } 3.6 V, R_L = 50 \Omega, C_L = 5 pF$		-	20	ı	
Total Jitter <sup>d</sup>	tJ			-	200	-	
Power Supply							
Power Supply Range	V+			2.6	-	4.3	V
Power Supply Current	I+	$V_{IN} = 0 \text{ V, or V+}$	Full	-	-	2	μΑ

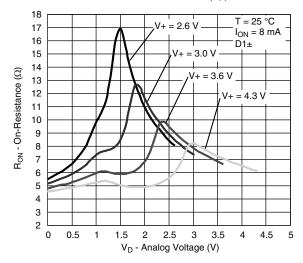
### **Notes**

- a. Room = 25  $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, not subjected to production test.
- e.  $V_{\text{IN}}$  = input voltage to perform proper function.
- f. Crosstalk measured between channels

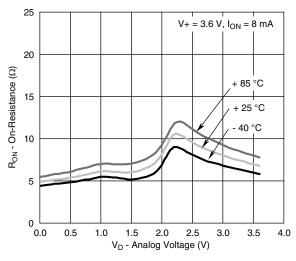
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



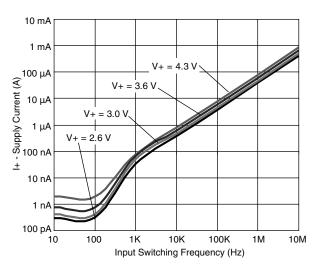
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



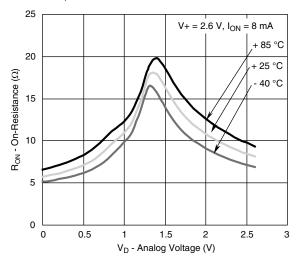
On-Resistance vs. V<sub>D</sub> and Single Supply Voltage



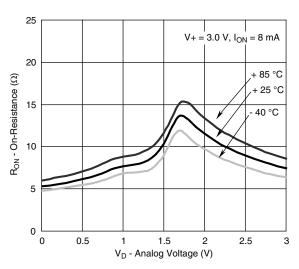
On-Resistance vs. Analog Voltage and Temperature



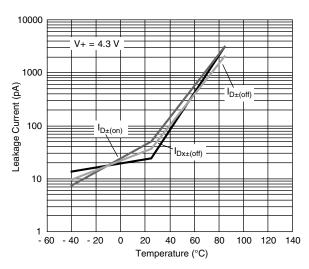
**Supply Current vs. Input Switching Frequency** 



On-Resistance vs. Analog Voltage and Temperature



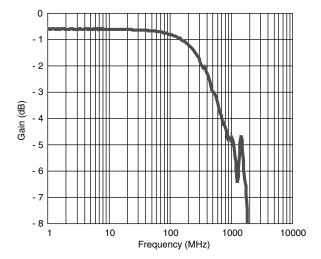
On-Resistance vs. Analog Voltage and Temperature



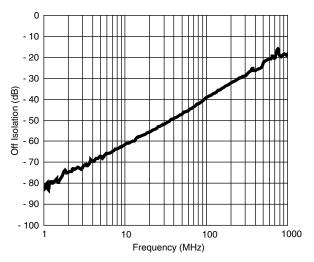
Leakage Current vs. Temperature



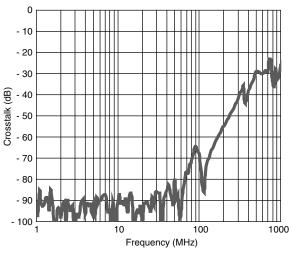
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Gain vs. Frequency,  $C_L = 5 pF$ , V+ = 3.3 V

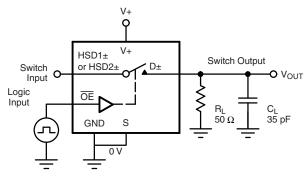


OFF Isolation, V+ = 3.3 V



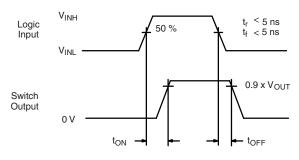
Crosstalk, V+ = 3.3 V

## **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = D \pm \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time



## **TEST CIRCUITS**

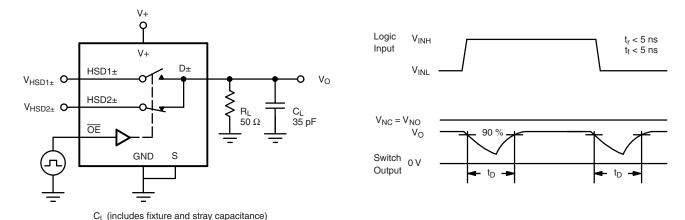


Fig. 2 - Break-Before-Make Interval

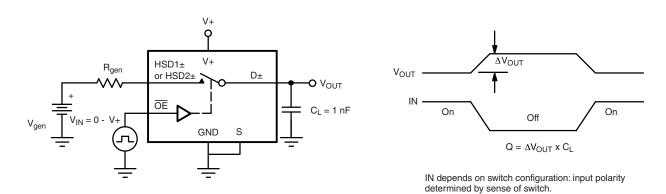


Fig. 3 - Charge Injection

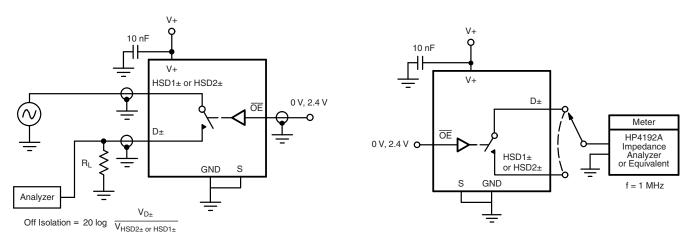


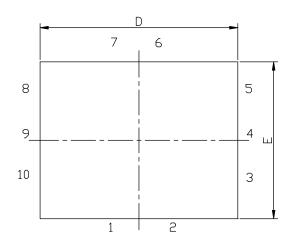
Fig. 4 - Off-Isolation

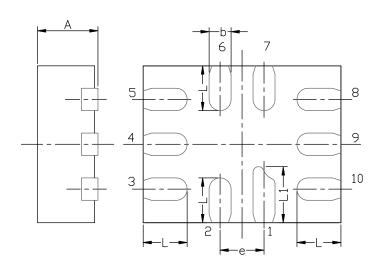
Fig. 5 - Channel Off/On Capacitance

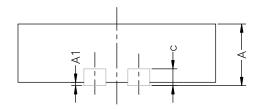
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg274593">www.vishay.com/ppg274593</a>.

Vishay Siliconix

## MINI QFN-10L CASE OUTLINE







DIM	MILLIMETERS			INCHES		
	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.
A	0.45	0.55	0.60	0.0177	0.0217	0.0236
A1	0.00	-	0.05	0.000	-	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.150 or 0.127 REF <sup>(1)</sup>			0.006 or 0.005 REF <sup>(1)</sup>		
D	1.70	1.80	1.90	0.067	0.071	0.075
E	1.30	1.40	1.50	0.051	0.055	0.059
е		0.40 BSC			0.016 BSC	
L	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217

## Note

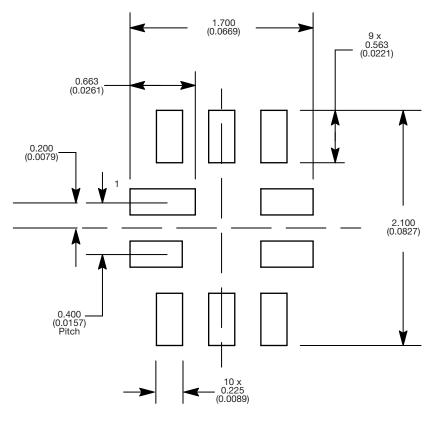
(1) The dimension depends on the leadframe that assembly house used.

ECN T16-0163-Rev. B, 16-May-16 DWG: 5957



Vishay Siliconix

## **RECOMMENDED MINIMUM PADS FOR MINI QFN 10L**



Mounting Footprint Dimensions in mm (inch)



# **Legal Disclaimer Notice**

Vishay

## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.